

## AMENDMENTS TO THE CLAIMS

1. (Currently Amended) A process of growing a thin film of  $\text{Al}_2\text{O}_3$  on a substrate having a surface in a reaction chamber by a sequential vapor deposition process comprising a plurality of cycles, each cycle comprising, in order:

- exposing the substrate in the reaction chamber to gaseous trimethyl aluminum (TMA), such that more than one monolayer of TMA forms on the substrate surface;
- stopping provision of the gaseous TMA;
- removing gaseous TMA from the reaction chamber;
- exposing the substrate in the reaction chamber to atomic oxygen; and
- removing atomic oxygen from the reaction chamber[.];
- wherein in each cycle more than one monolayer of  $\text{Al}_2\text{O}_3$  is formed.

2. (Currently Amended) The process of [[c]]Claim 1, wherein in each cycle a layer of  $\text{Al}_2\text{O}_3$  3 Å thick is formed.

3. (Previously Presented) The process of Claim 1, wherein the atomic oxygen is generated remotely in a radical generator.

4. (Original) The process of Claim 1, wherein the process is carried out at room temperature.

5. - 20. (Cancelled)